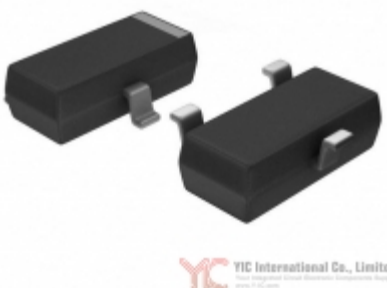


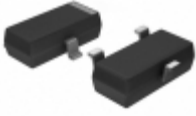




	<p>SI2323DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2323DS-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET P-CH 20V 3.7A SOT23-3</p>
	<p>Datenblätter:  SI2323DS-T1-GE3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 173118 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
<p>Image may be representation. See specs for product details.</p>	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SI2323DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 3.7A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	173118 pcs Stock
detaillierte Beschreibung	P-Channel 20V 3.7A (Ta) 750mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.7A (Ta)
Rds On (Max) @ Id, Vgs	39 mOhm @ 4.7A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	19nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	1020pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2323DS-T1-GE3CT

SI2323DS-T1-GE3 ist neu im Original, Suche SI2323DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2323DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2323DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2323DS VISHAY SI2323DS VISHAY</p>	 <p>SI2323DS-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 3.7A SOT23-3</p>	 <p>SI2324 Vishay Precision Group SI2324 VISHAY</p>	 <p>SI2323DS-T1 Vishay / Siliconix MOSFET P-CH 20V 3.7A SOT23</p>
 <p>SI2323DS-T1-E3 VIS VIS SOT-23</p>	 <p>SI2324DS-T1-E3 VISHAY SI2324DS-T1-E3 VISHAY</p>	 <p>SI2323DS-T1 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 3.7A SOT23</p>	 <p>SI2323DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 3.7A SOT23-3</p>

heiße Teile

Mehr

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|--------------------|--------------------|--------------------|--------------------|-------------------|
| ⊛ SI2319CDS-T1-GE3 | ↔ SI2319CDS-T1-GE3 | ⇒ SI2319DDS-T1-GE3 | D SI2319DS | ↔ SI2319DS-T1-E3 |
| ⊣ SI2319DS-T1-E3 | ⊛ SI2319DS-T1-GE3 | D SI2319DS-T1-GE3 | ⇒ SI2320DS | ↔ SI2320DS-T1-E3 |
| ⊛ SI2320DS-T1-GE3 | ⊣ SI2321DS-T1-E3 | ⊛ SI2321DS-T1-E3 | ↔ SI2321DS-T1-GE3 | ↔ SI2321DS-T1-GE3 |
| D SI2323CDS-T1 | ⊛ SI2323CDS-T1-E3 | ⊣ SI2323CDS-T1-GE3 | ⊛ SI2323CDS-T1-GE3 | ↔ SI2323DDS-T1-E3 |
| ⇒ SI2323DDS-T1-GE3 | ↔ SI2323DDS-T1-GE3 | ⊛ SI2323DS | ⊣ SI2323DS-T1-E3 | ↔ SI2323DS-T1-E3 |
| ↔ SI2323DS-T1-GE3 | ⇒ SI2324DS-T1-E3 | D SI2324DS-T1-GE3 | ⊛ SI2324DS-T1-GE3 | ⊣ SI2325DS-T1-E3 |
| ⊛ SI2325DS-T1-E3 | D SI2325DS-T1-GE3 | ⇒ SI2325DS-T1-GE3 | ↔ SI2327DS-T1-E3 | ↔ SI2327DS-T1-E3 |
| ⊣ SI2327DS-T1-GE3 | ⊛ SI2327DS-T1-GE3 | ↔ SI2328DS | ⇒ SI2328DS-T1 | ↔ SI2328DS-T1-E3 |
| ⊛ SI2328DS-T1-E3 | ⊣ SI2328DS-T1-GE3 | ⊛ SI2328DS-T1-GE3 | D SI2329DS-T1-E3 | ↔ SI2329DS-T1-GE3 |
| ↔ SI2329DS-T1-GE3 | ⊛ SI2331DS | ⊣ SI2331DS-T1-E3 | ⊛ SI2331DS-T1-E3 | ↔ SI2331DS-T1-GE3 |

Contact us:Info@Y-IC.com

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